

5 **In the Claims:**

Applicants hereby submit amended claims, including a complete listing of all claims in the application with the status of each claim in parentheses.

1.- 2. (canceled)

10 3. (canceled)

4. (canceled)

5. (canceled)

6. (canceled)

7. (previously presented) A method for formation of an ion beam that provides
15 carbon deposition over a substrate, the ion beam produced by inductively ionizing an acetylene plasma within a plasma volume and capacitatively coupling the plasma so as to form a stream of ions from within the plasma volume, the method comprising:

moving a magnetic field through the plasma volume to promote even resonant inductive ionization and homogenize the ion beam which deposits carbon over the substrate, wherein the
20 magnetic field rotates with a frequency of less than 10,000 Hz.

8. (previously presented) A method as claimed in claim 7, wherein moving the magnetic field comprises selectively energizing magnetic coils disposed about the plasma volume.

9. (previously presented) A method as claimed in claim 7, wherein the magnetic
25 field rotates through the plasma volume with a frequency which is much less than the frequency of an alternating induction potential within the plasma volume.

- 5 10. (previously presented) A method as claimed in claim 7, wherein the magnetic field is transverse and rotates about an axis which is substantially normal to a capacitatively coupled extraction grid within the plasma volume.
11. (previously presented) A method as claimed in claim 7, wherein the magnetic field rotates with a frequency of less than 100 Hz.
- 10 12.-15. (canceled).
16. (canceled)
17. (canceled)
18. (previously presented) A method as in claim 7, wherein the carbon is deposited on the substrate at a rate in a range from 20 Å per second to 100 Å per second.
- 15 19. (canceled)
20. (canceled)
21. (previously presented) A method as in claim 7, wherein the substrate includes a magnetic recording medium.
22. (previously presented) A method as in claim 7, wherein the substrate includes a
- 20 semiconductor material.
23. (canceled)
24. (canceled)
25. (canceled)
26. (canceled)
- 25 27. (canceled)
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| 5 | 30. | (canceled) |
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| | 34. | (canceled) |
| 10 | 35. | (canceled) |
| | 36. | (canceled) |
| | 37. | (canceled) |
| | 38. | (canceled) |
| | 39. | (canceled) |
| 15 | 40. | (canceled) |